

### KSD1616/1616A

# **Audio Frequency Power Amplifier & Medium Speed Switching**

• Complement to KSB1116/1116A



## **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parame	Ratings	Units	
V <sub>CBO</sub>	Collector-Base Voltage	: KSD1616 : KSD1616A	60 120	V V
V <sub>CEO</sub>	Collector-Emitter Voltage	: KSD1616 : KSD1616A	50 60	V V
V <sub>EBO</sub>	Emitter-Base Voltage		6	V
I <sub>C</sub>	Collector Current (DC)		1	Α
I <sub>CP</sub>	* Collector Current (Pulse)		2	Α
P <sub>C</sub>	Collector Power Dissipation		0.75	W
TJ	Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature		-55 ~ 150	°C

<sup>\*</sup> PW≤10ms, Duty Cycle < 50%

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =60V, $I_{E}$ =0			100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> =6V, I <sub>C</sub> =0			100	nA
h <sub>FE1</sub>	DC Current Gain : KSD1616	V <sub>CE</sub> =2V, I <sub>C</sub> =100mA	135		600	
	: KSD1616A		135		400	
$h_{FE2}$		V <sub>CE</sub> =2V, I <sub>C</sub> =1A	81			
V <sub>BE</sub> (on)	* Base-Emitter On Voltage	$V_{CE}$ =2V, $I_{C}$ =50mA	600	640	700	mV
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> =1A, I <sub>B</sub> =50mA		0.15	0.3	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	I <sub>C</sub> =1A, I <sub>B</sub> =50mA		0.9	1.2	V
C <sub>ob</sub>	Output Capacitance	V <sub>CE</sub> =10V, I <sub>E</sub> =0, f=1MHz		19		pF
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =2V, I <sub>C</sub> =100mA	100	160		MHz
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> =10V, I <sub>C</sub> =100mA		0.07		μs
t <sub>STG</sub>	Storage Time	I <sub>B1</sub> = -I <sub>B2</sub> =10mA		0.95		μs
t <sub>F</sub>	Fall Time	$V_{BE}$ (off) = -2~-3V		0.07		μs

<sup>\*</sup> Pulse Test: PW<350μs, Duty Cycle≤2% Pulsed

### **h**<sub>FE1</sub> Classification

Classification	Y	G	L
h <sub>FE1</sub>	135 ~ 270	200 ~ 400	300 ~ 600

## **Typical Characteristics**

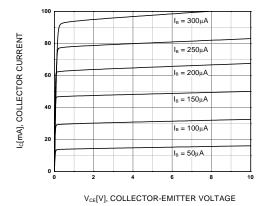


Figure 1. Static Characteristic

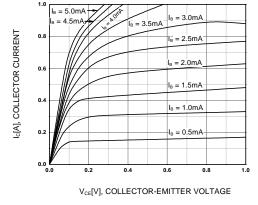


Figure 2. Static Characteristic

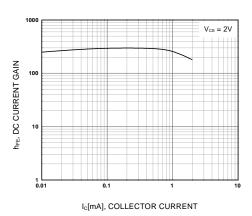


Figure 3. DC current Gain

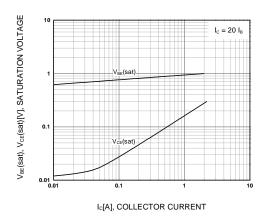


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

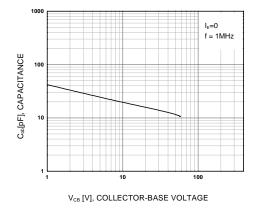


Figure 5. Collector Output Capacitance

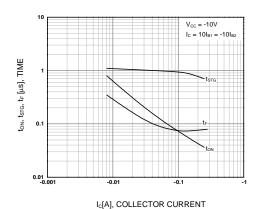


Figure 6. Switching Time

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## **Typical Characteristics** (Continued)

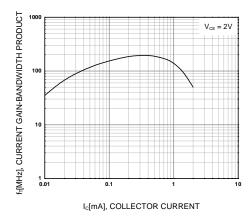


Figure 7. Current Gain Bandwidth Product

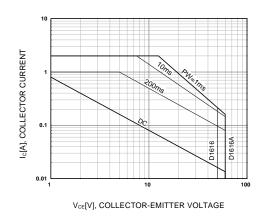


Figure 8. Safe Operating Area

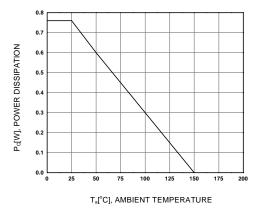
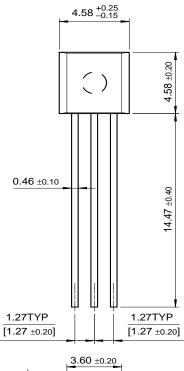


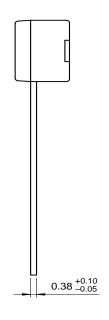
Figure 9. Power Derating

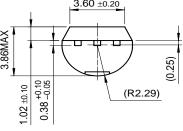
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## **Package Dimensions**

TO-92







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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
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